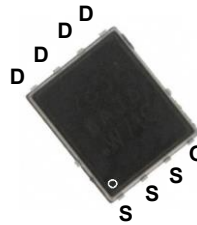
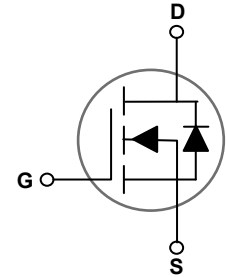


## Main Product Characteristics

$BV_{DSS}$	100V
$R_{DS(ON)}$	9m $\Omega$
$I_D$	62A



PPAK5x6



Schematic Diagram

## Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



## Description

The GSFP0976 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

## Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	+20/-12	V
Drain Current-Continuous ( $T_C=25^\circ\text{C}$ )	$I_D$	62	A
Drain Current-Continuous ( $T_C=100^\circ\text{C}$ )		39.2	
Drain Current-Pulsed <sup>1</sup>	$I_{DM}$	248	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	211	mJ
Single Pulse Avalanche Current <sup>2</sup>	$I_{AS}$	65	A
Power Dissipation ( $T_C=25^\circ\text{C}$ )	$P_D$	125	W
Power Dissipation-Derate above 25 $^\circ\text{C}$		1	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1	$^\circ\text{C}/\text{W}$
Operating Junction Temperature Range	$T_J$	-55 To +150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 To +150	$^\circ\text{C}$

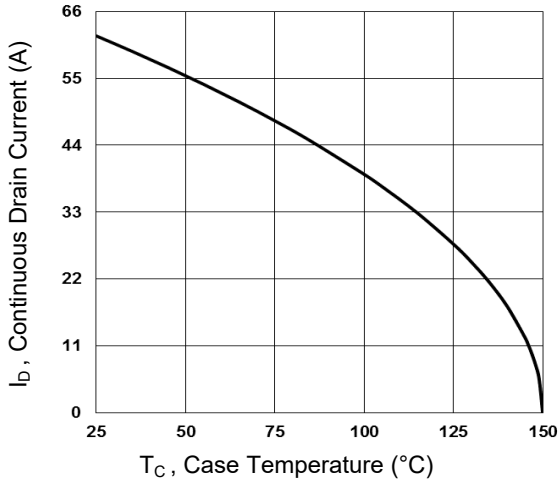
**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>On/Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
$BV_{DSS}$ Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^{\circ}\text{C}$ , $I_D=1mA$	-	0.054	-	$V/^{\circ}\text{C}$
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V,$ $T_J=25^{\circ}\text{C}$	-	-	1	$\mu A$
		$V_{DS}=80V, V_{GS}=0V,$ $T_J=85^{\circ}\text{C}$	-	-	10	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=+20V, V_{DS}=0V$	-	-	100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=15A$	-	7.2	9	m $\Omega$
		$V_{GS}=10V,$ $I_D=15A (T_J=125^{\circ}\text{C})$	-	11.8	-	
		$V_{GS}=4.5V, I_D=8A$	-	10.8	14	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		-	-5.5	-	mV/ $^{\circ}\text{C}$
Forward Transconductance	$g_{fs}$	$V_{DS}=10V, I_D=3A$	-	11	-	S
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge <sup>3,4</sup>	$Q_g$	$V_{DS}=50V, I_D=8.5A,$ $V_{GS}=10V$	-	37.8	76	nC
Gate-Source Charge <sup>3,4</sup>	$Q_{gs}$		-	7.8	16	
Gate-Drain Charge <sup>3,4</sup>	$Q_{gd}$		-	8.4	17	
Turn-On Delay Time <sup>3,4</sup>	$t_{d(on)}$	$V_{DD}=50V, R_G=6\Omega,$ $V_{GS}=10V, I_D=1A$	-	14.6	30	nS
Rise Time <sup>3,4</sup>	$t_r$		-	21.5	44	
Turn-Off Delay Time <sup>3,4</sup>	$t_{d(off)}$		-	54	108	
Fall Time <sup>3,4</sup>	$t_f$		-	84.3	168	
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V,$ $F=1MHz$	-	2250	4500	pF
Output Capacitance	$C_{oss}$		-	410	820	
Reverse Transfer Capacitance	$C_{rss}$		-	25	50	
Gate Resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V,$ $F=1MHz$	-	1.43	-	$\Omega$
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Continuous Source Current	$I_S$	$V_G=V_D=0V,$	-	-	62	A
Pulsed Source Current	$I_{SM}$	Force Current	-	-	124	A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=1A,$ $T_J=25^{\circ}\text{C}$	-	-	1	V
Reverse Recovery Time	$t_{rr}$	$V_{GS}=0V, I_S=10A,$ $di/dt=100A/\mu s,$ $T_J=25^{\circ}\text{C}$	-	49.2	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	75.1	-	nC

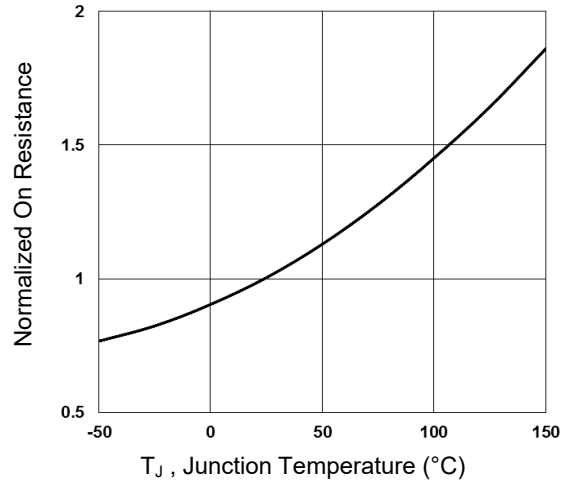
Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2.  $V_{DD}=50V, V_{GS}=10V, L=0.1mH, I_{AS}=65A, R_G=25\Omega,$  starting  $T_J=25^{\circ}\text{C}$ .
3. Pulse test: pulse width  $\leq 300\mu s,$  duty cycle  $\leq 2\%$ .
4. Essentially independent of operating temperature.

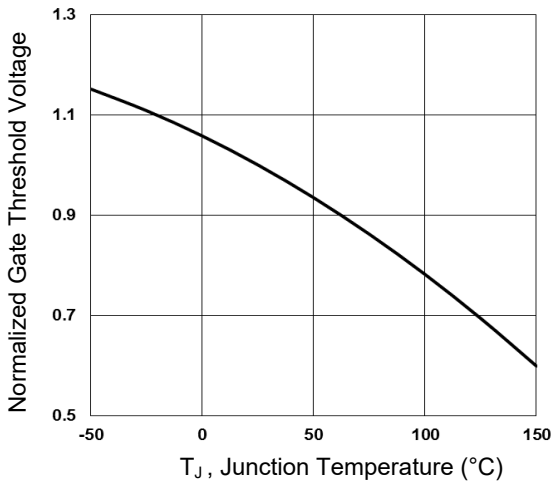
**Typical Electrical and Thermal Characteristic Curves**



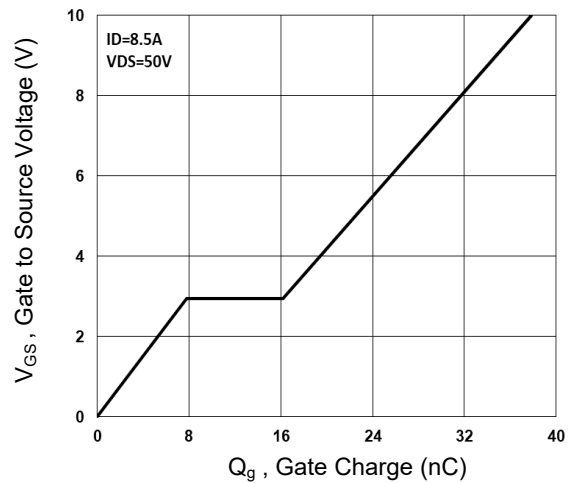
**Figure 1. Continuous Drain Current vs.  $T_C$**



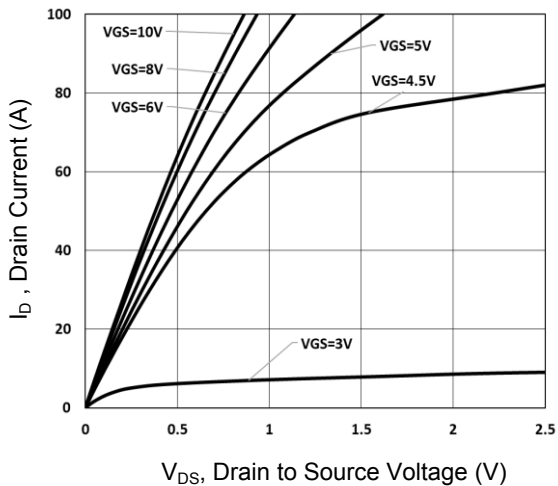
**Figure 2. Normalized  $R_{DSON}$  vs.  $T_J$**



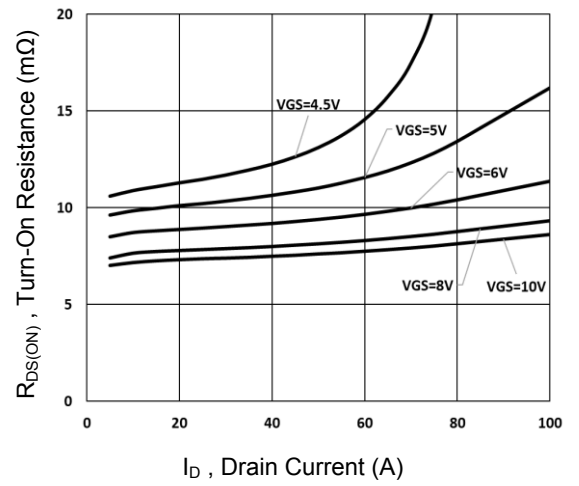
**Figure 3. Normalized  $V_{th}$  vs.  $T_J$**



**Figure 4. Gate Charge Waveform**

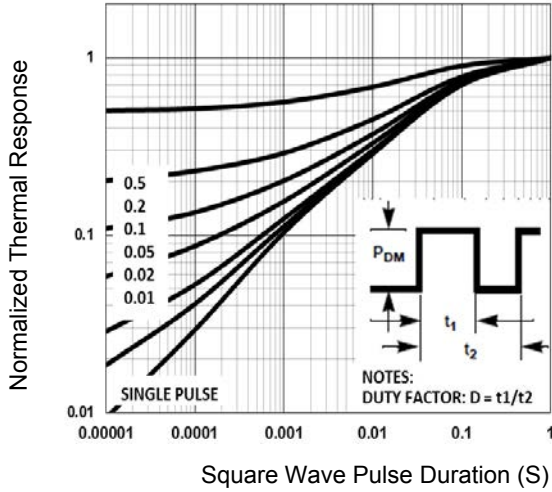


**Figure 5. Typical Output Characteristics**

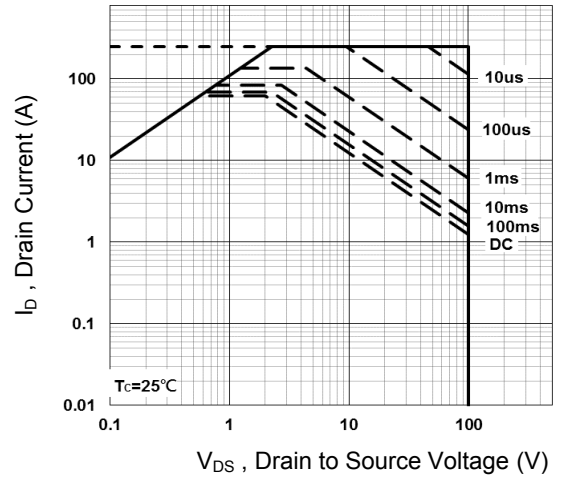


**Figure 6. Turn-On Resistance vs.  $I_D$**

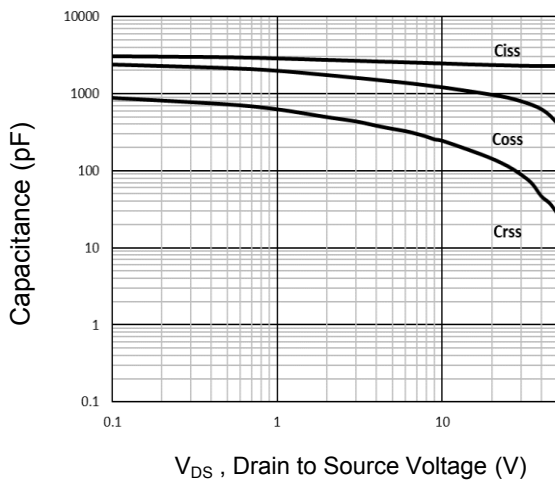
**Typical Electrical and Thermal Characteristic Curves**



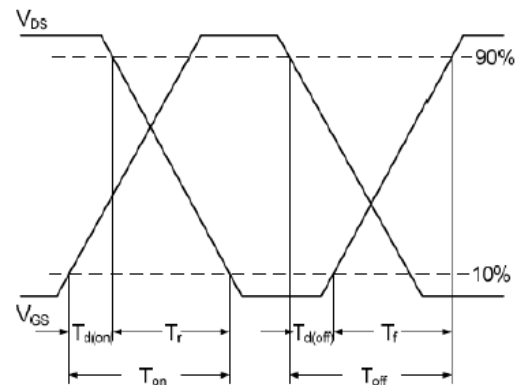
**Figure 7. Normalized Transient Impedance**



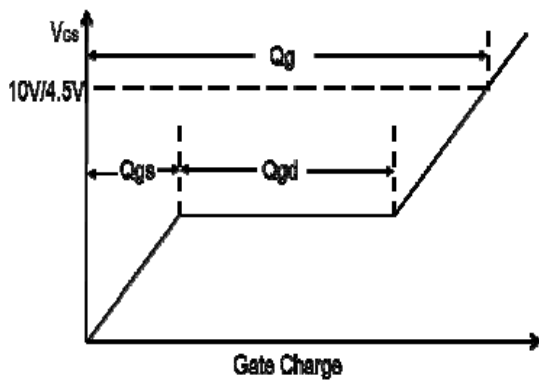
**Figure 8. Maximum Safe Operation Area**



**Figure 9. Capacitance Characteristics**



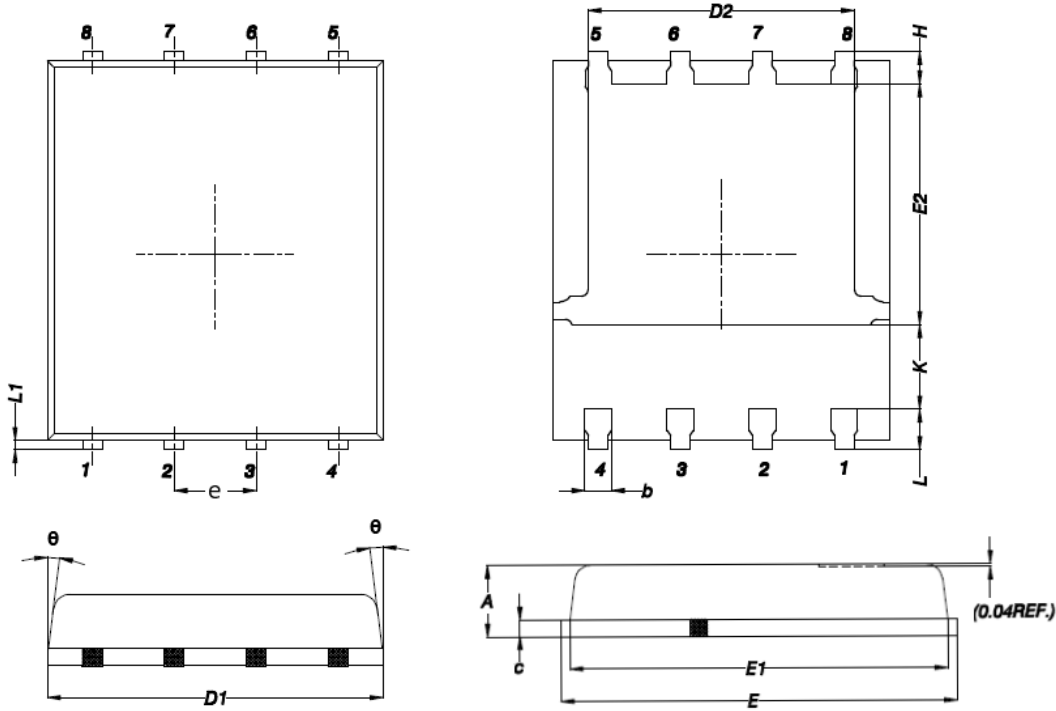
**Figure 10. Switching Time Waveform**



**Figure 11. Gate Charge Waveform**

**Package Outline Dimensions**

**PPAK5x6**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.200	0.850	0.047	0.031
b	0.510	0.300	0.020	0.012
C	0.300	0.200	0.012	0.008
D1	5.400	4.800	0.212	0.189
D2	4.310	3.610	0.170	0.142
E	6.300	5.850	0.248	0.230
E1	5.960	5.450	0.235	0.215
E2	3.920	3.300	0.154	0.130
e	1.27BSC		0.05BSC	
H	0.650	0.380	0.026	0.015
K	---	1.100	---	0.043
L	0.710	0.380	0.028	0.015
L1	0.250	0.050	0.009	0.002
θ	12°	0°	12°	0°